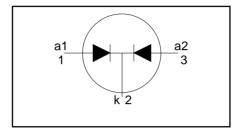
Dual rectifier diodes ultrafast

BYV34 series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 300 \text{ V/ } 400 \text{ V/ } 500 \text{ V}$$
 $V_F \le 1.05 \text{ V}$
 $I_{O(AV)} = 20 \text{ A}$
 $t_{rr} \le 60 \text{ ns}$

GENERAL DESCRIPTION

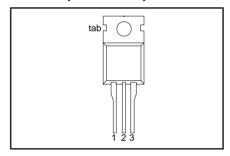
Dual, common cathode, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV34 series is supplied in the conventional leaded SOT78 (TO220AB) package.

PINNING

PIN	DESCRIPTION		
1	anode 1		
2	cathode		
3	anode 2		
tab	cathode		

SOT78 (TO220AB)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V _{RRM} V _{RWM} V _R	Peak repetitive reverse voltage Crest working reverse voltage Continuous reverse voltage	$\label{eq:total_bound} \textbf{BYV34}$ $\label{eq:total_bound} \textbf{T}_{mb} \leq 138 ^{\circ} \textbf{C}$	- - -	- 300 300 300 300	-400 400 400 400	-500 500 500 500	V V V
$I_{O(AV)}$ I_{FRM}	Average rectified output current (both diodes conducting) ¹ Repetitive peak forward current	T _{mb} ≤ 115 °C	-		20 20		A A
I _{FSM}	per diode Non-repetitive peak forward current per diode.	$T_{mb} \le 115$ °C t = 10 ms t = 8.3 ms sinusoidal; with reapplied	- -		120 132		A A
T _{stg}	Storage temperature Operating junction temperature	V _{RRM(max)}	-40 -		150 150		°C °C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-hs}$ $R_{th j-a}$	heatsink	per diode both diodes conducting in free air.	1 1 1	- - 60	2.4 1.6 -	K/W K/W K/W

¹ Neglecting switching and reverse current losses

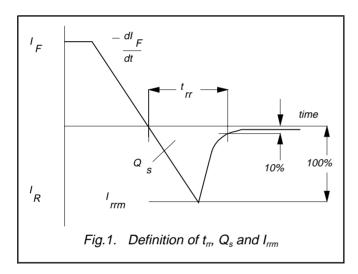
Dual rectifier diodes ultrafast

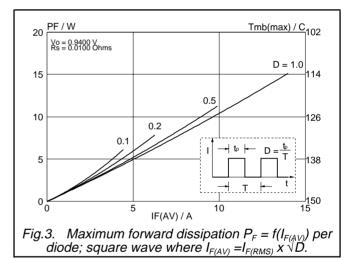
BYV34 series

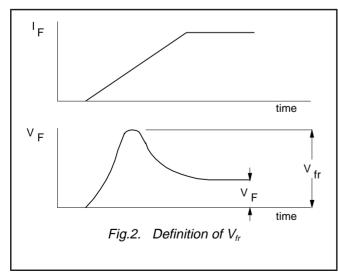
ELECTRICAL CHARACTERISTICS

characteristics are per diode at T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	$I_F = 10 \text{ A}; T_j = 150^{\circ}\text{C}$	-	0.87	1.05	V
•	1	$I_{\rm F} = 20 \text{A}$	-	1.10	1.35	V
I _R	Reverse current	$V_R = V_{RRM}$	-	10	50	μΑ
		$V_{R} = V_{RRM}$; $T_{j} = 100 ^{\circ}C$ $I_{F} = 2 ^{\circ}A ^{\circ}to ^{\circ}V_{R} \geq 30 ^{\circ}V$;	-	0.2	0.6	mΑ
Q_s	Reverse recovery charge	$I_F = 2 \text{ Å to } V_R \ge 30 \text{ V};$	-	50	60	nC
Ü		$dI_F/dt = 20 A/\mu s$				
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A to } V_R \ge 30 \text{ V};$	-	50	60	ns
	·	dl _F /dt = 100 A/μs				
I _{rrm}	Peak reverse recovery current	$I_{\rm F} = 10 \text{ A to V}_{\rm R} \ge 30 \text{ V};$	-	4.0	5.0	Α
	ĺ	$dI_{E}/dt = 50 \text{ A/us}$: $T_{i} = 100^{\circ}\text{C}$				
V_{fr}	Forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$	-	2.5	-	V







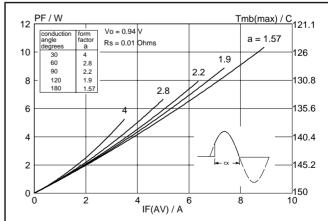
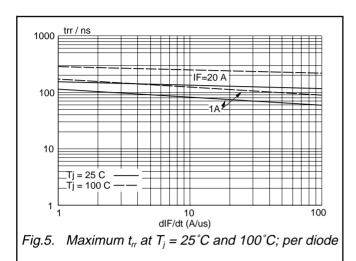
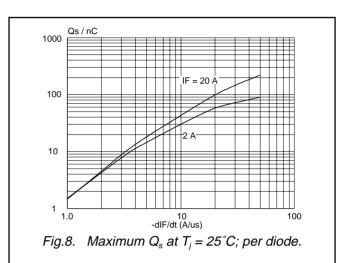


Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor = $I_{F(RMS)} / I_{F(AV)}$.

Dual rectifier diodes ultrafast

BYV34 series





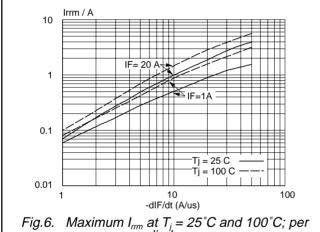


Fig.6. Maximum I_{rm} at $T_j = 25^{\circ}C$ and $100^{\circ}C$; per diode.

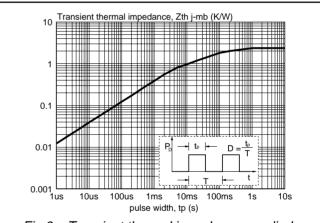


Fig.9. Transient thermal impedance per diode $Z_{th j-mb} = f(t_p)$

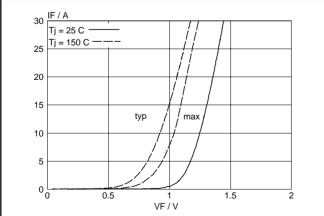
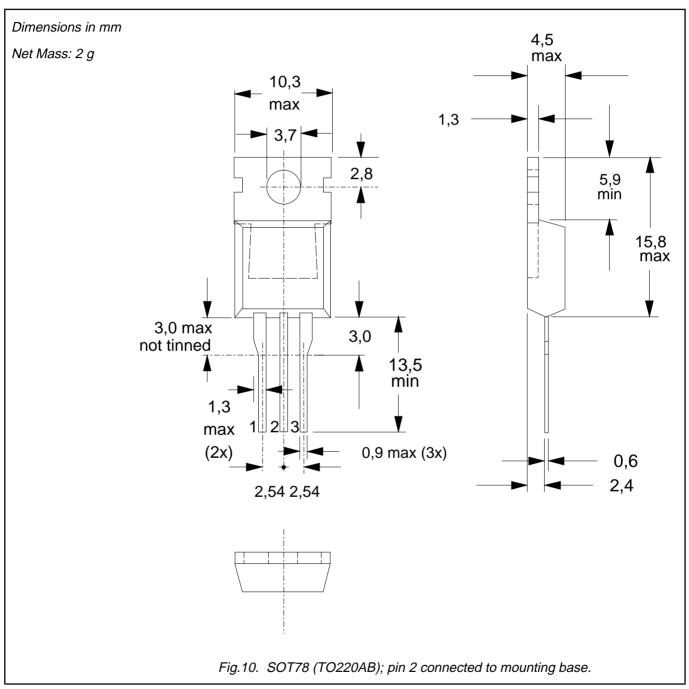


Fig.7. Typical and maximum forward characteristic

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for SOT78 (TO220) envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Dual rectifier diodes ultrafast

BYV34 series

DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la					
Product specification This data sheet contains final product specifications.					
Limiting values					

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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